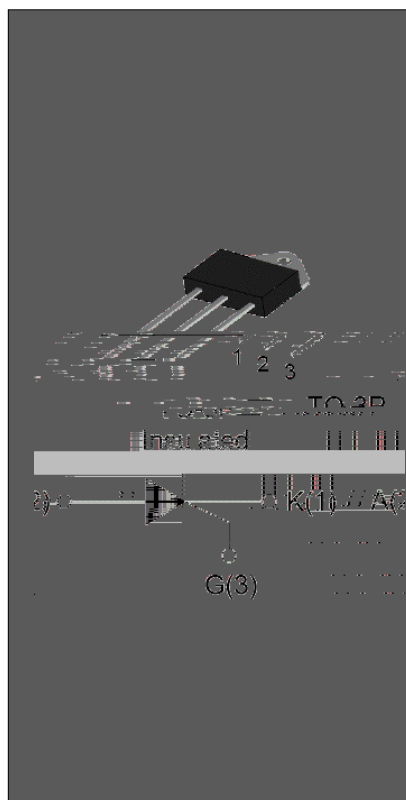




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1055Z SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1055Z provides a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	55	A
V_{DRM}/V_{RRM}	1000	V
I_{GT}	50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1000	V
Average on-state current ($T_c = 60^\circ\text{C}$)	$I_{T(AV)}$	35	A
RMS on-state current ($T_c = 60^\circ\text{C}$)	$I_{T(RMS)}$	55	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I_{TSM}	700	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}, T_j=25^\circ\text{C}$)		750	
I^2t value for fusing ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I^2t	2450	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100\text{Hz}, T_j=125^\circ\text{C}$)	di/dt	200	$\text{A}/\mu\text{s}$



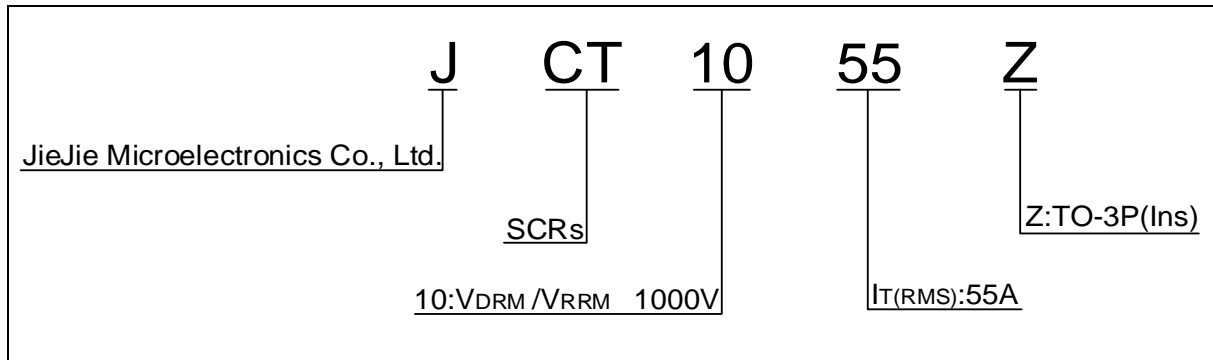
Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	50	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3K$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	120	mA
I_H	$I_T=500mA$	-	-	100	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125$	1500	-	-	V/ μs
t_{on}	$I_G=50mA$ $I_A=500mA$ $I_R=50mA$ $T_j=25$	-	4	-	μs =5 1
t_{off}		-	130	-	

T =5

ORDERING INFORMATION



MARKING

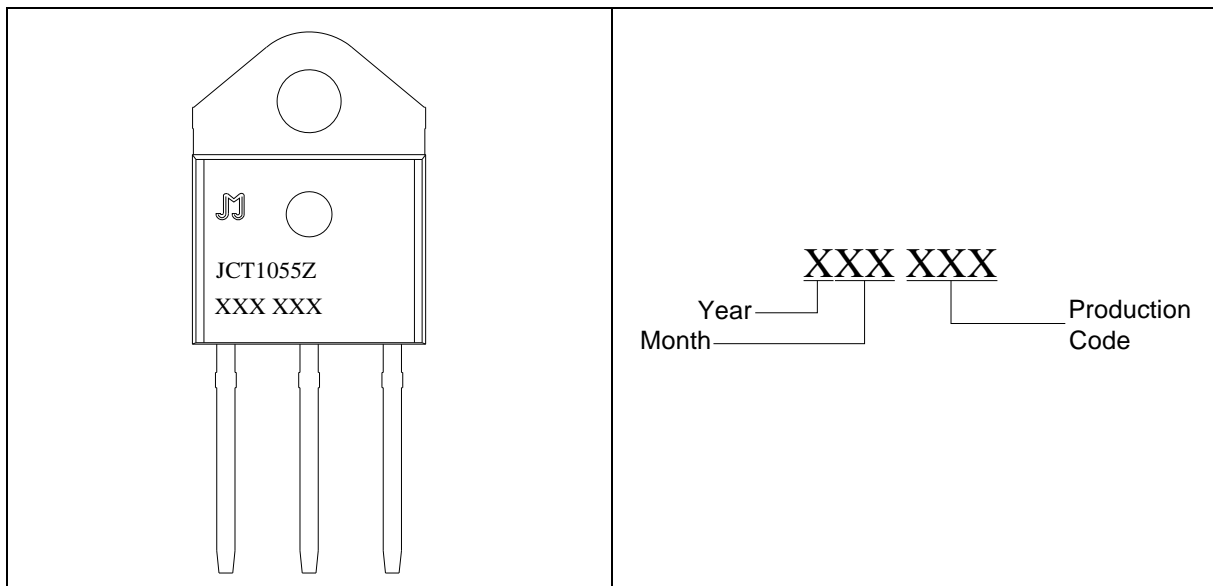


FIG.1 Maximum power dissipation versus RMS on-state current

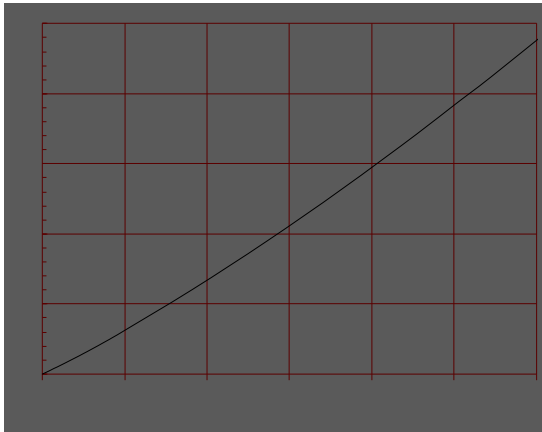


FIG.2: RMS on-state current versus case temperature

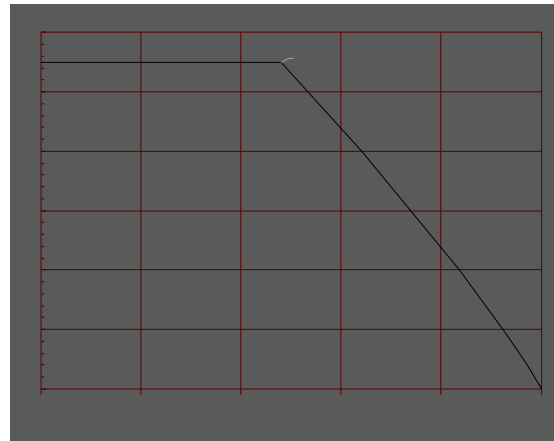


FIG.3: Surge peak on-state current versus number of cycles

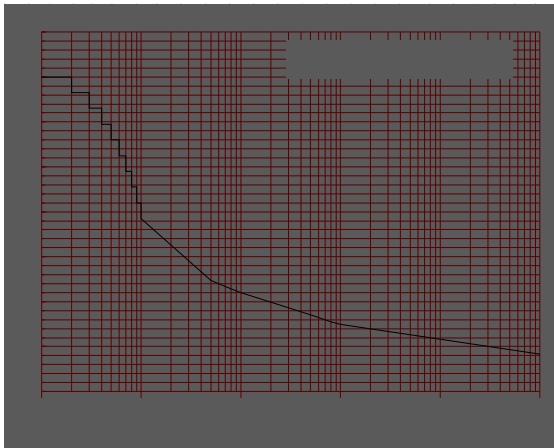


FIG.4: On-state characteristics

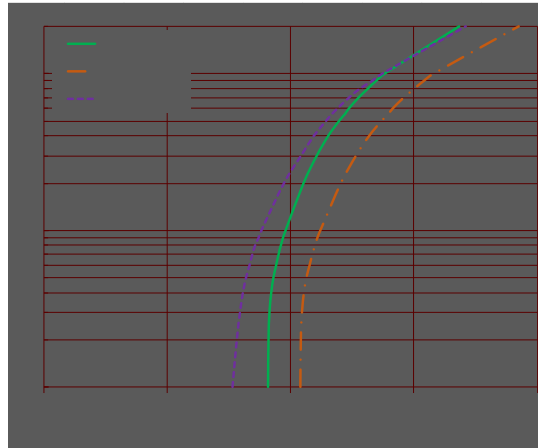


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 200\text{A}/\mu\text{s}$)

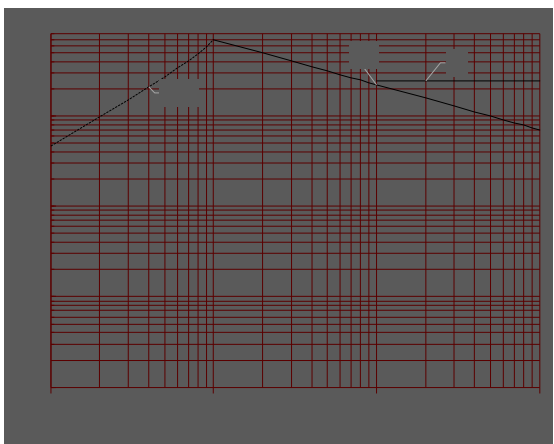


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

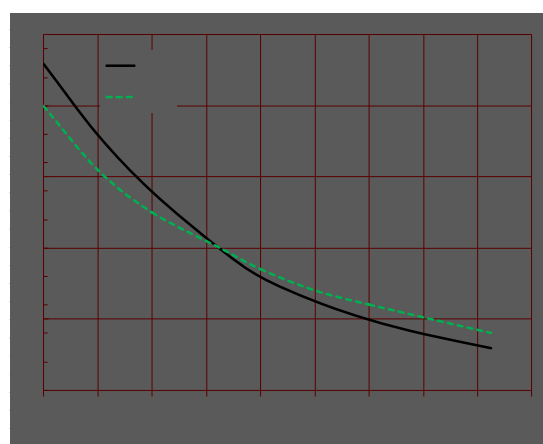
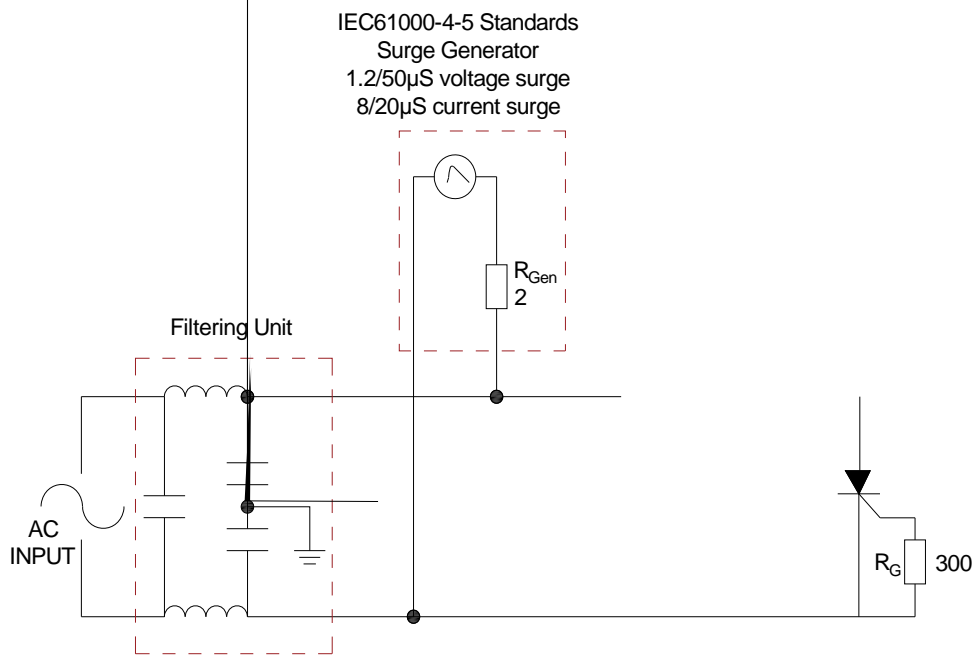


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



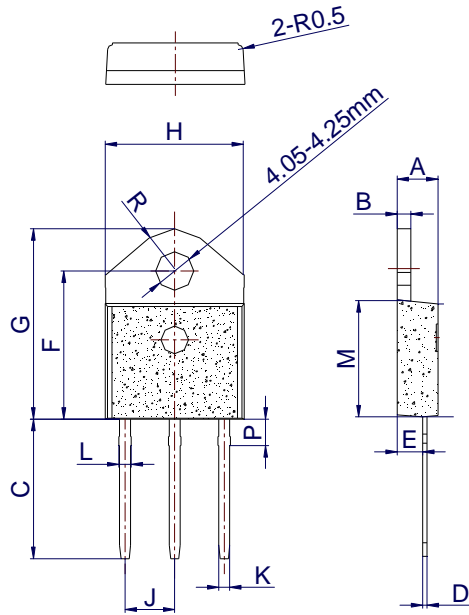
**ORDERING INFORMATION**

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1055Z	1000	50	TO-3P(Ins)	30	Tube

Document Revision History

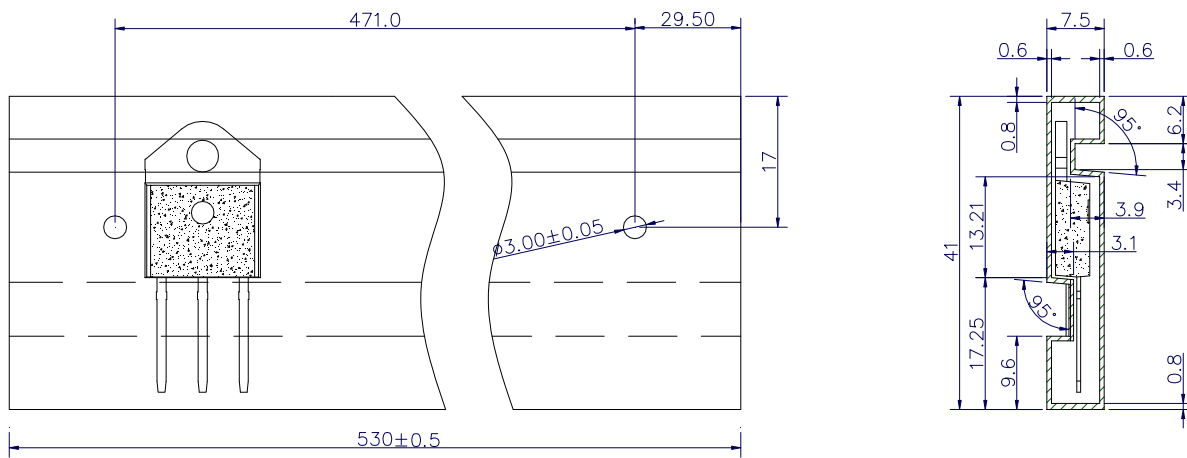
Date	Revision	Changes
May.17, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250



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